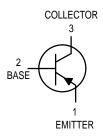
# **Amplifier Transistors PNP Silicon**



### **MAXIMUM RATINGS**

Rating	Symbol	BC 212	BC 213	BC 214	Unit
Collector-Emitter Voltage	VCEO	-50	-30	-30	Vdc
Collector-Base Voltage	Vсво	-60	-45	-45	Vdc
Emitter-Base Voltage	VEBO	-5.0			Vdc
Collector Current — Continuous	lC	-100			mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	350 2.8			mW mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	1.0 8.0		Watts mW/°C	
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>Stg</sub>	-55 to +150			°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	125	°C/W

### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = -2.0 mAdc, I <sub>B</sub> = 0)	BC212 BC213 BC214	V(BR)CEO	-50 -30 -30	_ _ _	_ _ _	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = -10 μA, I <sub>E</sub> = 0)	BC212 BC213 BC214	V(BR)CBO	-60 -45 -45	_ _ _	_ _ _	Vdc
Emitter-Base Breakdown Voltage ( $I_E = -10 \mu Adc, I_C = 0$ )	BC212 BC213 BC214	V(BR)EBO	-5 -5 -5	_ 		Vdc
Collector–Emitter Leakage Current (V <sub>CB</sub> = -30 V)	BC212 BC213 BC214	ICBO	_ _ _	_ _ _	–15 –15 –15	nAdc
Emitter–Base Leakage Current (V <sub>EB</sub> = -4.0 V, I <sub>C</sub> = 0)	BC212 BC213 BC214	I <sub>EBO</sub>			–15 –15 –15	nAdc

# BC212,B BC213 BC214



### BC212,B BC213 BC214

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Тур	Max	Unit	
ON CHARACTERISTICS							
DC Current Gain (I <sub>C</sub> = $-10 \mu$ Adc, V <sub>CE</sub> = $-5.0 \text{ Vdc}$ )	BC212 BC213 BC214	hFE	40 40 100	_ _ _	_ _ _	_	
(I <sub>C</sub> = $-2.0$ mAdc, V <sub>CE</sub> = $-5.0$ Vdc)	BC212 BC213 BC214		60 80 140	_ _ _	— — 600		
$(I_C = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})(1)$	BC212, BC214 BC213		_ _	120 140	_ _		
Collector-Emitter Saturation Voltage (I <sub>C</sub> = -10 mAdc, I <sub>B</sub> = -0.5 mAdc) (I <sub>C</sub> = -100 mAdc, I <sub>B</sub> = -5.0 mAdc)(1)		VCE(sat)	_ _	-0.10 -0.25	_ 	Vdc	
Base-Emitter Saturation Voltage (I <sub>C</sub> = -100 mAdc, I <sub>B</sub> = -5.0 mAdc)		V <sub>BE(sat)</sub>	_	-1.0	-1.4	Vdc	
Base–Emitter On Voltage (I <sub>C</sub> = -2.0 mAdc, V <sub>CE</sub> = -5.0 Vdc)		VBE(on)	-0.6	-0.62	-0.72	Vdc	
DYNAMIC CHARACTERISTICS			•	•			
Current-Gain — Bandwidth Product (I <sub>C</sub> = -10 mAdc, V <sub>CE</sub> = -5.0 Vdc, f = 100 MHz)	BC212 BC214 BC213	fT	_ _ _	280 320 360	_ _ _	MHz	
Common–Base Output Capacitance (V <sub>CB</sub> = -10 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)		C <sub>ob</sub>	_	_	6.0	pF	
Noise Figure (IC = $-0.2$ mAdc, VCE = $-5.0$ Vdc, RS = $2.0$ k $\Omega$ , f = $1.0$ kHz)	BC214	NF	_	_	2	dB	
(I <sub>C</sub> = $-0.2$ mAdc, V <sub>CE</sub> = $-5.0$ Vdc, R <sub>S</sub> = $2.0$ kΩ, f = $1.0$ kHz, f = $200$ Hz)	BC212, BC213		_	_	10		
Small–Signal Current Gain (IC = -2.0 mAdc, VCE = -5.0 Vdc, f = 1.0 kHz)	BC212 BC213 BC214 BC212B	h <sub>fe</sub>	60 80 140 200	_ _ _ _	   400	_	

<sup>1.</sup> Pulse Test: Tp 300 s, Duty Cycle 2.0%.

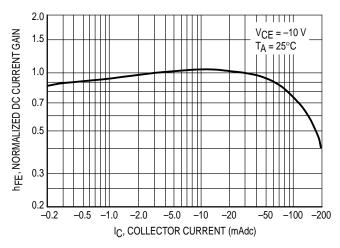


Figure 1. Normalized DC Current Gain

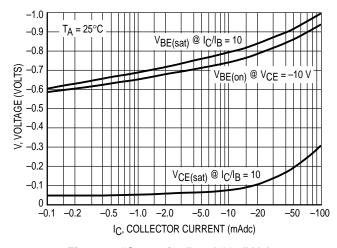


Figure 2. "Saturation" and "On" Voltages

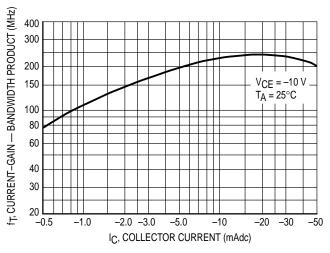


Figure 3. Current-Gain — Bandwidth Product

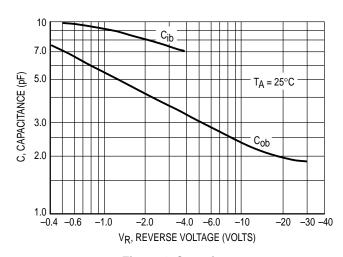


Figure 4. Capacitances

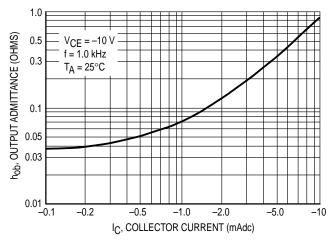


Figure 5. Output Admittance

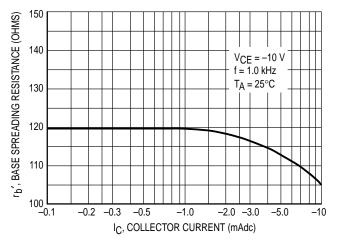
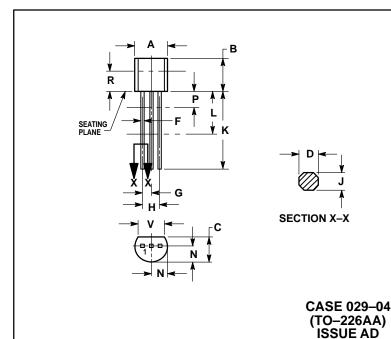


Figure 6. Base Spreading Resistance

### PACKAGE DIMENSIONS



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K
  MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.022	0.41	0.55	
F	0.016	0.019	0.41	0.48	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100	_	2.54	
R	0.115		2.93		
V	0.135		3 43		

STYLE 17:

PIN 1. COLLECTOR

2. BASE
 EMITTER

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